



Typical Applications

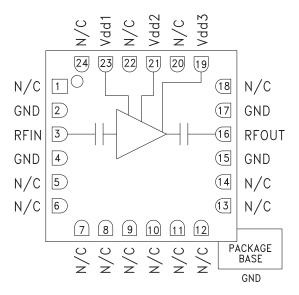
The HMC517LC4 is ideal for use as a LNA or driver amplifier for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- Test Equipment and Sensors
- Military

Features

Noise Figure: 2.5 dB Gain: 19 dB OIP3: +23 dBm Single Supply: +3V @ 67 mA 50 Ohm Matched Input/Output RoHS Compliant 4 x 4 mm Package

Functional Diagram



General Description

The HMC517LC4 chip is a high dynamic range GaAs PHEMT MMIC Low Noise Amplifier (LNA) housed in a leadless "Pb free" RoHS compliant SMT package. The HMC517LC4 provides 19 dB of small signal gain, 2.5 dB of noise figure and has an output IP3 of +23 dBm. The P1dB output power of +13 dBm enables the LNA to also function as a LO driver for balanced, I/Q or image reject mixers. The HMC517LC4 allows the use of surface mount manufacturing techniques.

HMC517LC4

SMT PHEMT LOW NOISE AMPLIFIER, 17 - 26 GHz

Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd 1, 2, 3 = +3V

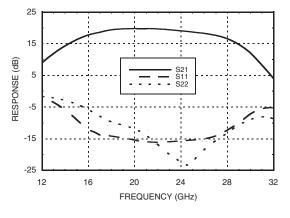
Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		17 - 22		22 - 26		GHz	
Gain	16	19		15	18		dB
Gain Variation Over Temperature		0.02	0.03		0.02	0.03	dB/ °C
Noise Figure		2.5	3.1		2.6	3.3	dB
Input Return Loss		15			15		dB
Output Return Loss		11			17		dB
Output Power for 1 dB Compression (P1dB)		12			13		dBm
Saturated Output Power (Psat)		15			16		dBm
Output Third Order Intercept (IP3)		23			24		dBm
Supply Current (Idd)(Vdd = +3V)		67			67		mA



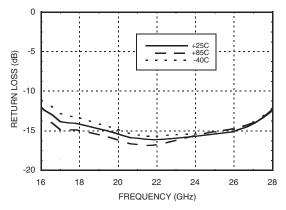
SMT PHEMT LOW NOISE AMPLIFIER, 17 - 26 GHz



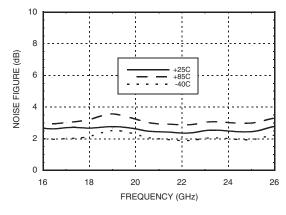
Broadband Gain & Return Loss



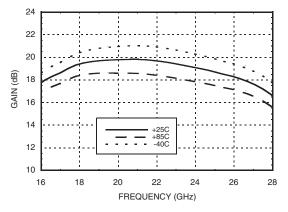
Input Return Loss vs. Temperature



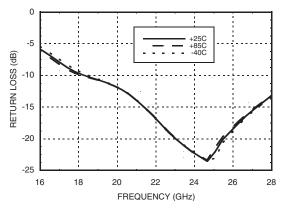
Noise Figure vs. Temperature



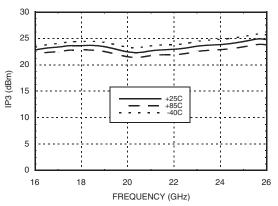
Gain vs. Temperature



Output Return Loss vs. Temperature



Output IP3 vs. Temperature



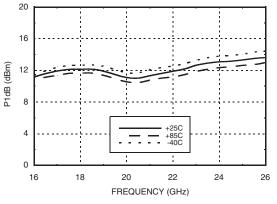
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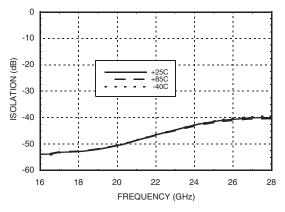


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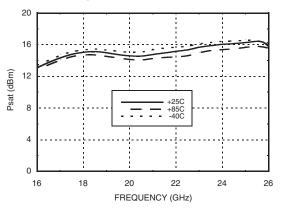




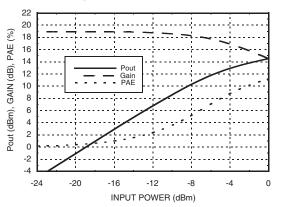
Reverse Isolation vs. Temperature



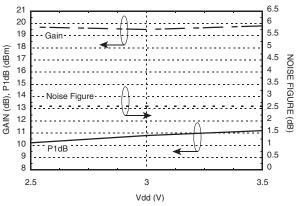
Psat vs. Temperature



Power Compression @ 21 GHz







For price, delivery, and to place orders, please contact Hittite Microwave Corporation: 20 Alpha Road, Chelmsford, MA 01824 Phone: 978-250-3343 Fax: 978-250-3373 Order On-line at www.hittite.com





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Absolute Maximum Ratings

Drain Bias Voltage (Vdd1, Vdd2, Vdd3)	+5.5 Vdc	
RF Input Power (RFIN)(Vdd = +3.0 Vdc)	+2 dBm	
Channel Temperature	175 °C	
Continuous Pdiss (T= 85 °C) derate 29 mW/°C above 85 °C) 2.65 W		
Thermal Resistance (channel to die bottom)	34 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	
ESD Sensitivity (HBM)	Class 1A	

Typical Supply Current vs. Vdd

Vdd (Vdc)	ldd (mA)	
+2.5	66	
+3.0	68	
+3.5	71	

Note: Amplifier will operate over full voltage range shown above.



BOTTOM VIEW

ELECTROSTATIC SENSITIVE DEVICE **OBSERVE HANDLING PRECAUTIONS**

Outline Drawing

PIN 24 0.157±0.005 .014 .009 0.36 .013 [0.32] REF [4.00±0.13] 24 19 PIN 1 000000 PIN 1 18 \square 0.157±0.005 [4.00±0.13] H51D 2.56 D 0.56 .022 017. __ D X X X X.101 D 6 13 \square $\Box \Box \Box \Box \Box$ (I) 12 .098 [2.50] LOT NUMBER SQUARE EXPOSED 0.040 [1.02] GROUND -.122 [3.10] —• MAX PADDLE SEATING PLANE -C-NOTES: 1. PACKAGE BODY MATERIAL: ALUMINA 2. LEAD AND GROUND PADDLE PLATING: 30-80 MICROINCHES GOLD OVER 50 MICROINCHES MINIMUM NICKEL 3. DIMENSIONS ARE IN INCHES [MILLIMETERS]

4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE

5. PACKAGE WARP SHALL NOT EXCEED 0.05mm DATUM 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE

SOLDERED TO PCB RF GROUND

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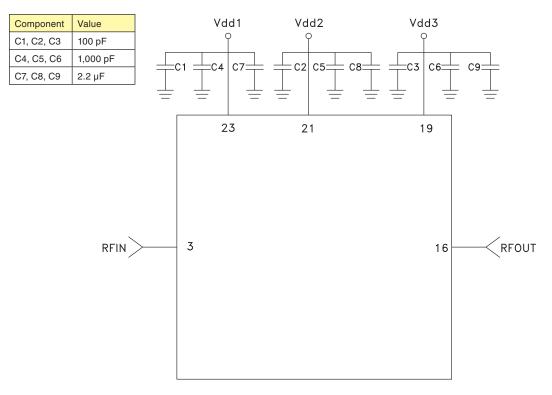


SMT PHEMT LOW NOISE AMPLIFIER, 17 - 26 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 5-14, 18, 20, 22, 24	N/C	This pin may be connected to RF/DC ground. Performance will not be affected.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms from 17 - 26 GHz.	
23, 21, 19	Vdd1, 2, 3	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, 1,000 pF and 2.2 μF are required.	0 Vdd1,2,3
16	RFOUT	This pin is AC coupled and matched to 50 Ohms from 17 - 26 GHz.	
2, 4, 15, 17	GND	These pins and package bottom must be connected to RF/DC ground.	

Application Circuit



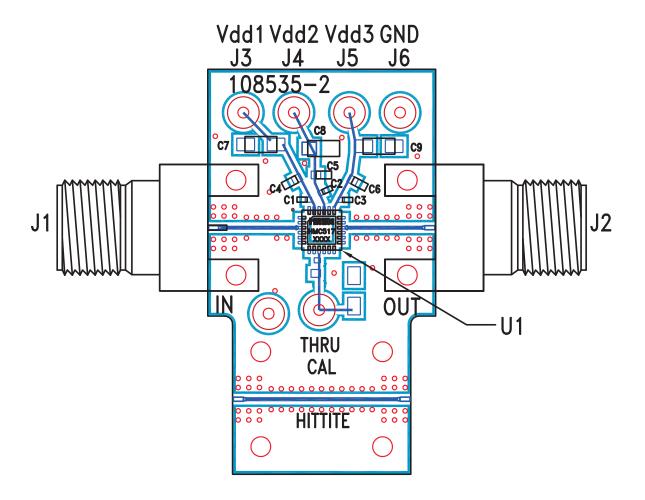
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ROHS

Evaluation PCB



List of Materials for Evaluation PCB 108537 [1]

Item	Description	
J1 - J2	PCB Mount K Connector	
J3 - J6	DC Pin	
C1 - C3	100 pF Capacitor, 0402 Pkg.	
C4 - C6	1,000 pF Capacitor, 0603 Pkg.	
C7 - C9	2.2 µF Capacitor, Tantalum	
U1	HMC517LC4 Amplifier	
PCB [2]	108535 Evaluation PCB	

Reference this number when ordering complete evaluation PCB
Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.